

# XP234N08013R-G

ETR11056-001a

### N-channel MOSFET 30V, 0.8A

#### **■**FEATURES

On-State Resistance :  $R_{DS}(on)=0.29\Omega$  @V<sub>GS</sub> =10V

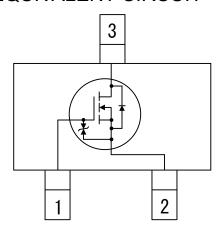
Driving voltage : 4.5\

Environmentally Friendly : EU RoHS Compliant, Pb Free

#### APPLICATIONS

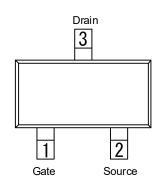
Switching

### ■ EQUIVALENT CIRCUIT



### ■ PIN CONFIGURATION

●SOT-323-3A



#### ■ PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT
XP234N08013R-G *	SOT-323-3A	3,000pcs/ Reel

<sup>\*</sup> The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

#### ■ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (DC)	I <sub>D</sub>	0.8	Α
Drain Current(Pulse) (*1)	I <sub>DP</sub>	1.6	Α
Channel Power Dissipation (*2)	$P_d$	0.35	W
Junction Temperature	TJ	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C

<sup>\*(1)</sup> PW≦10µs,duty cycle≦1%

<sup>\*(\*2)</sup> When implemented on a PCB defined by JESD51-7

## XP234N08013R-G

## **■**ELECTRICAL CHARACTERISTICS

Ta=25°C

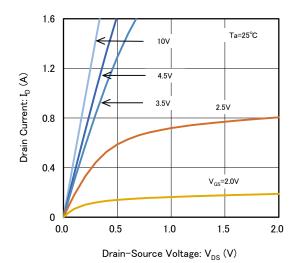
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	30	-	-	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	-	-	1	μA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V	-	-	±10	μA
Gate Threshold Voltage	$V_{GS(off)}$	I <sub>D</sub> = 250uA, V <sub>DS</sub> = V <sub>GS</sub>	0.9	1.7	2.6	V
Drain-Source On Resistance	В	V <sub>GS</sub> = 10V, I <sub>D</sub> = 400mA	-	0.2	0.29	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 400mA	-	0.3	0.4	Ω
Input Capacitance	Ciss	101/1/	-	64	-	pF
Output Capacitance	Coss	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f= 1MHz	-	16	-	pF
Reverse Transfer Capacitance	Crss	-	-	8	-	pF
Turn-on Delay Time	t <sub>d(on)</sub>		-	11	-	ns
Rise Time	tr	V <sub>DD</sub> = 10V, I <sub>D</sub> = 400mA	-	8	-	ns
Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> = 10V	-	70	-	ns
Fall Time	t <sub>f</sub>		-	30	-	ns
Total Gate Charge	Qg	\/ 40\/ L 400A	-	1.32	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> = 10V, I <sub>D</sub> = 400mA V <sub>GS</sub> = 10V	-	0.16	-	nC
Gate-Drain Charge	$Q_{gd}$	VGS- IUV	-	0.26	-	nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 400mA, V <sub>GS</sub> = 0V	-	0.7	1.1	V

## **■**NOTES ON USE

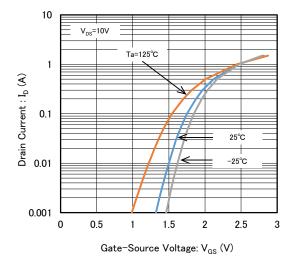
- Please use this IC within the absolute maximum ratings.
   Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.
- Torex places an importance on improving our products and their reliability.
   We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

## **■**TYPICAL PERFORMANCE CHARACTERISTICS

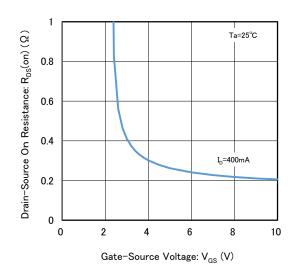
(1) Drain Current vs. Drain-Source Voltage



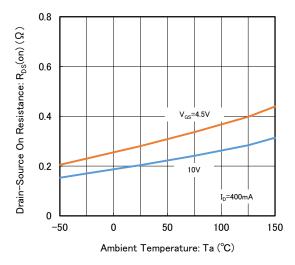
(2) Drain Current vs. Gate-Source Voltage



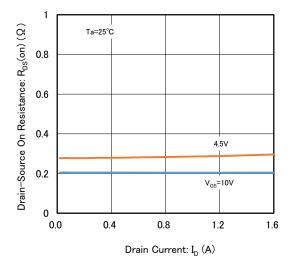
(3) Drain-Source On Resistance vs. Gate-Source Voltage



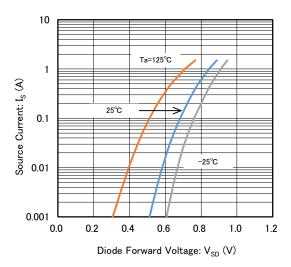
(4) Drain-Source On Resistance vs. Ambient Temperature



(5) Drain-Source On Resistance vs. Drain Current



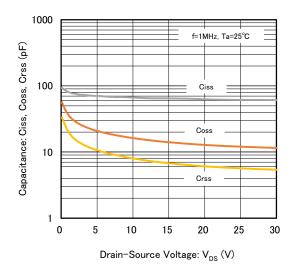
(6) Source Current vs. Diode Forward Voltage



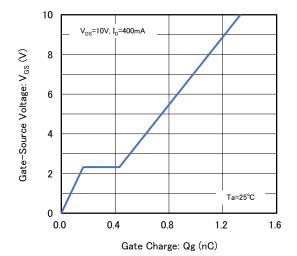
## XP234N08013R-G

## ■TYPICAL PERFORMANCE CHARACTERISTICS

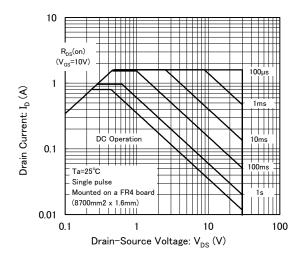
#### (7) Ciss, Coss, Crss vs. Drain-Source Voltage



#### (8) Gate-Source Voltage vs. Gate Charge



#### (9) Area of Safe Operation



## **■PACKAGING INFORMATION**

For the latest package information go to, <a href="www.torexsemi.com/technical-support/packages">www.torexsemi.com/technical-support/packages</a>

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-323-3A	<u>SOT-323-3A PKG</u>	JESD51-7 Board	SOT-323-3A Power Dissipation

## **■**MARKING RULE

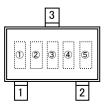
#### ●SOT-323-3A

①,②,③represents product series

MARK		PRODUCT SERIES	
1	2	3	PRODUCT SERIES
3	4	N	XP234N0801**-G

④,⑤ represents production lot number。
01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated (G, I, J, O, Q, W excluded)
\*No character inversion used

SOT-323-3A



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